



# FDMA8884

## Single N-Channel Power Trench<sup>®</sup> MOSFET

30 V, 6.5 A, 23 mΩ

### Features

- Max  $r_{DS(on)}$  = 23 mΩ at  $V_{GS} = 10$  V,  $I_D = 6.5$  A
- Max  $r_{DS(on)}$  = 30 mΩ at  $V_{GS} = 4.5$  V,  $I_D = 6.0$  A
- High performance trench technology for extremely low  $r_{DS(on)}$
- Fast switching speed
- RoHS Compliant

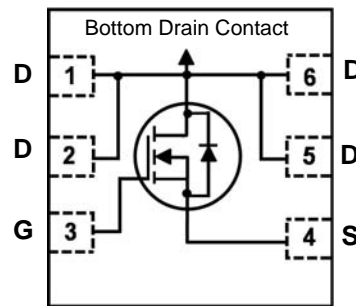
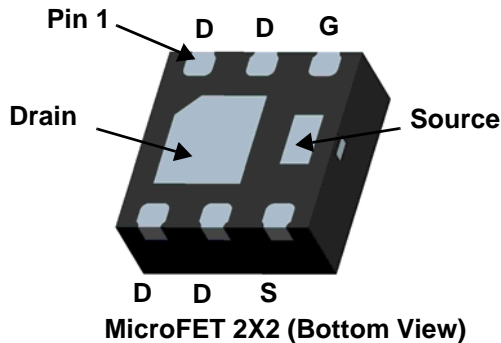


### General Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced Power Trench<sup>®</sup> process that has been optimized for  $r_{DS(on)}$  switching performance.

### Application

- Primary Switch



### MOSFET Maximum Ratings $T_A = 25$ °C unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{DS}$	Drain to Source Voltage	30	V
$V_{GS}$	Gate to Source Voltage (Note 3)	±20	V
$I_D$	Drain Current -Continuous (Package limited) $T_C = 25$ °C	8.0	A
	-Continuous $T_A = 25$ °C (Note 1a)	6.5	
	-Pulsed	25	
$P_D$	Power Dissipation (Note 1a)	1.9	W
	Power Dissipation (Note 1b)	0.7	
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150	°C

### Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	65	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1b)	180	

### Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
884	FDMA8884	MicroFET 2x2	7"	8 mm	3000 units

May 2014

FDMA8884 N-Channel Power Trench<sup>®</sup> MOSFET

**Electrical Characteristics**  $T_J = 25\text{ }^{\circ}\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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**Off Characteristics**

$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 250\text{ }\mu\text{A}$ , $V_{GS} = 0\text{ V}$	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$ , referenced to $25\text{ }^{\circ}\text{C}$		15		mV/ $^{\circ}\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 24\text{ V}$ , $V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
$I_{GSS}$	Gate to Source Leakage Current, Forward	$V_{GS} = 20\text{ V}$ , $V_{DS} = 0\text{ V}$			100	nA

**On Characteristics**

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = 250\text{ }\mu\text{A}$	1.2	1.8	3.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$ , referenced to $25\text{ }^{\circ}\text{C}$		-5		mV/ $^{\circ}\text{C}$
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{ V}$ , $I_D = 6.5\text{ A}$		19	23	m $\Omega$
		$V_{GS} = 4.5\text{ V}$ , $I_D = 6.0\text{ A}$		25	30	
		$V_{GS} = 10\text{ V}$ , $I_D = 6.5\text{ A}$ , $T_J = 125\text{ }^{\circ}\text{C}$		25	30	
$g_{FS}$	Forward Transconductance	$V_{DD} = 5\text{ V}$ , $I_D = 6.5\text{ A}$		26		S

**Dynamic Characteristics**

$C_{iss}$	Input Capacitance	$V_{DS} = 15\text{ V}$ , $V_{GS} = 0\text{ V}$ , $f = 1\text{ MHz}$		339	450	pF
$C_{oss}$	Output Capacitance			132	175	pF
$C_{rss}$	Reverse Transfer Capacitance			18	28	pF
$R_g$	Gate Resistance			1.1		$\Omega$

**Switching Characteristics**

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 15\text{ V}$ , $I_D = 6.5\text{ A}$ , $V_{GS} = 10\text{ V}$ , $R_{GEN} = 6\text{ }\Omega$		5	10	ns
$t_r$	Rise Time			1	10	ns
$t_{d(off)}$	Turn-Off Delay Time			11	20	ns
$t_f$	Fall Time			1	10	ns
$Q_{g(TOT)}$	Total Gate Charge	$V_{GS} = 0\text{ V to }10\text{ V}$	$V_{DD} = 15\text{ V}$ $I_D = 6.5\text{ A}$	5.4	7.5	nC
	Total Gate Charge	$V_{GS} = 0\text{ V to }4.5\text{ V}$		2.7	3.7	nC
$Q_{gs}$	Total Gate Charge			1.0		nC
$Q_{gd}$	Gate to Drain "Miller" Charge			0.9		nC

**Drain-Source Diode Characteristics**

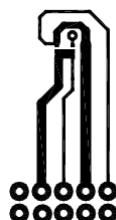
$V_{SD}$	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{ V}$ , $I_S = 6.5\text{ A}$ (Note 2)		0.86	1.2	V
$t_{rr}$	Reverse Recovery Time	$I_F = 6.5\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$		16	28	ns
$Q_{rr}$	Reverse Recovery Charge			4	10	nC

## NOTES:

1.  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



a.  $65\text{ }^{\circ}\text{C/W}$  when mounted on a  $1\text{ in}^2$  pad of 2 oz copper.



b.  $180\text{ }^{\circ}\text{C/W}$  when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width  $< 300\text{ }\mu\text{s}$ , Duty cycle  $< 2.0\%$ .

3. As an N-ch device, the negative  $V_{gs}$  rating is for low duty cycle pulse occurrence only. No continuous rating is implied.

# Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

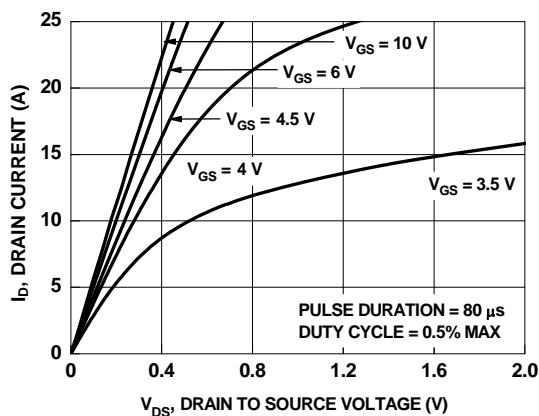


Figure 1. On Region Characteristics

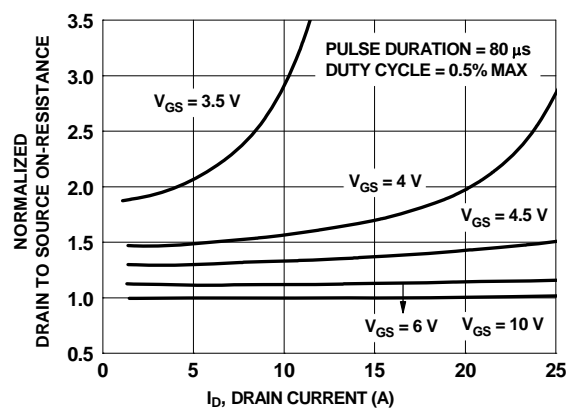


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

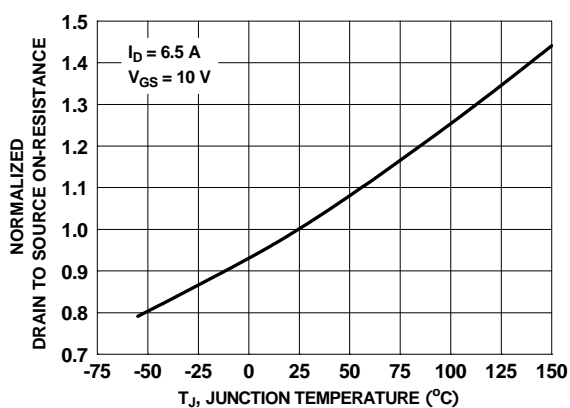


Figure 3. Normalized On Resistance vs Junction Temperature

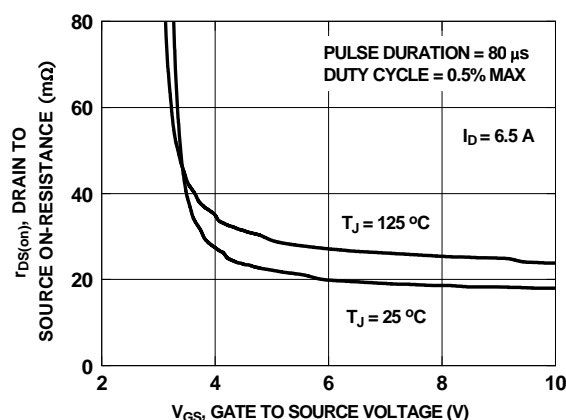


Figure 4. On-Resistance vs Gate to Source Voltage

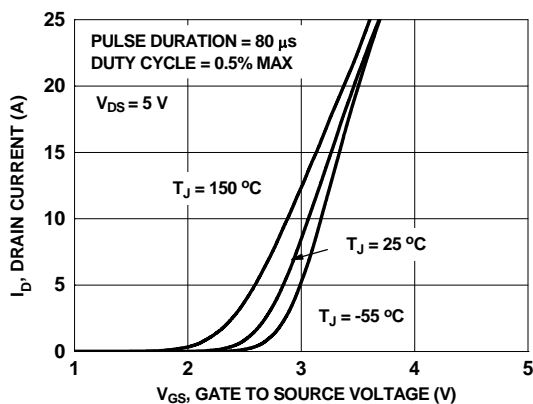


Figure 5. Transfer Characteristics

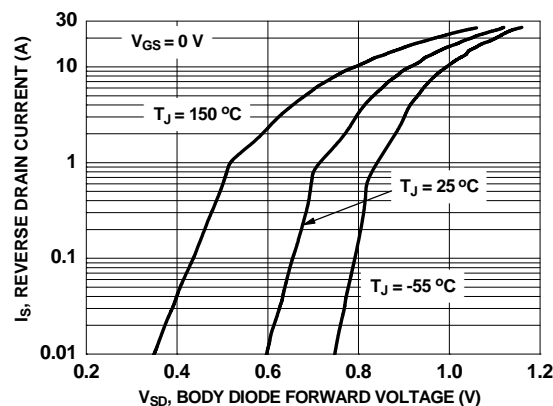


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

# Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

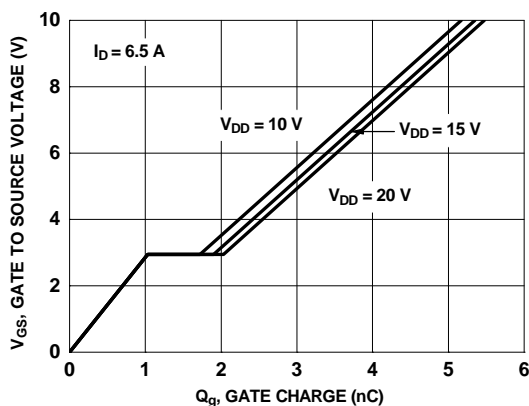


Figure 7. Gate Charge Characteristics

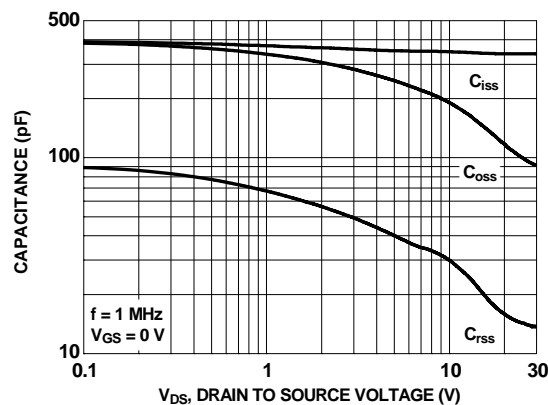


Figure 8. Capacitance vs Drain to Source Voltage

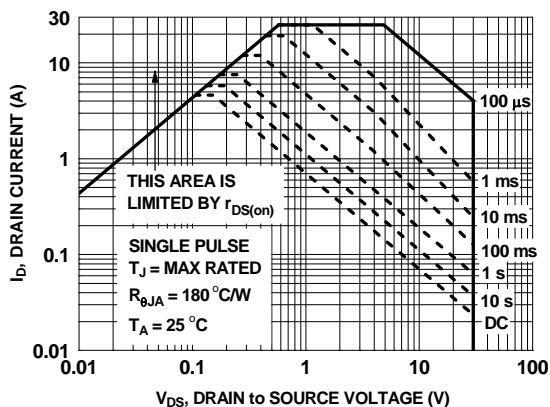


Figure 9. Forward Bias Safe Operating Area

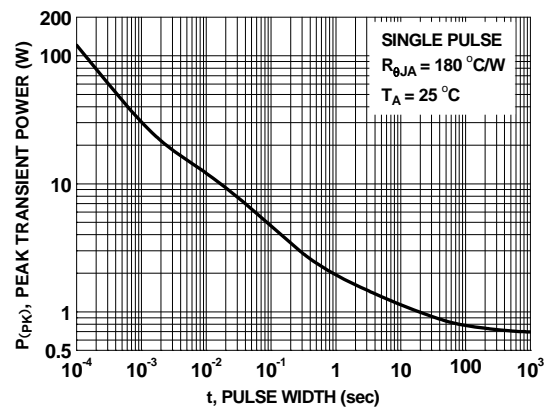


Figure 10. Single Pulse Maximum Power Dissipation

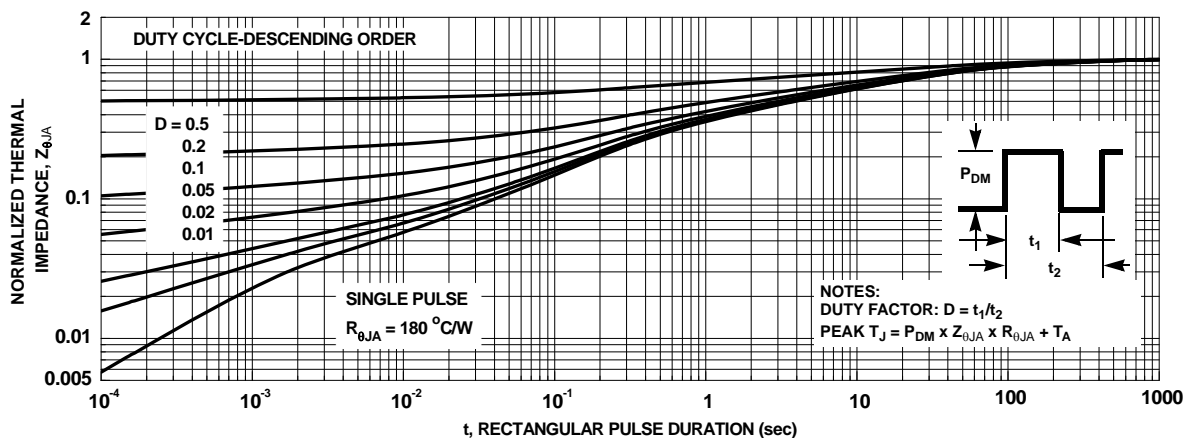
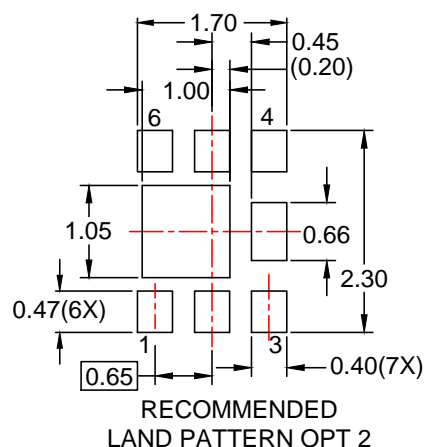
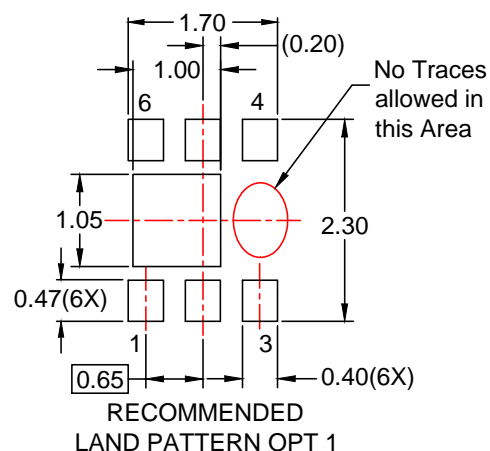
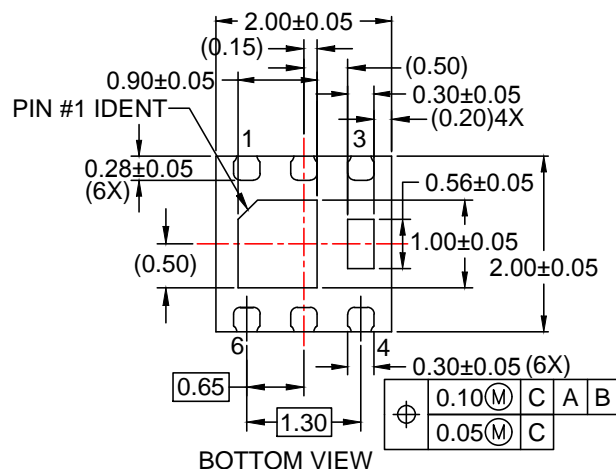
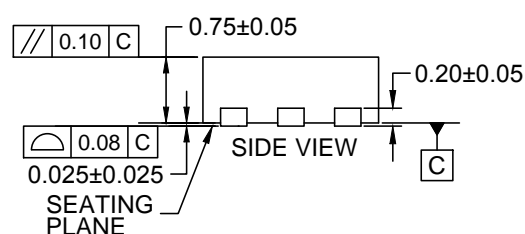
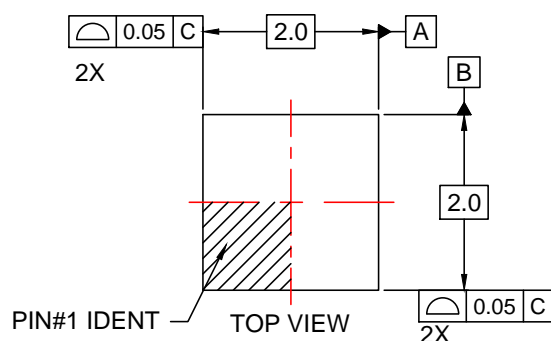


Figure 11. Junction-to-Ambient Transient Thermal Response Curve

Figure 12.

# Dimensional Outline and Pad Layout



## NOTES:

- PACKAGE DOES NOT FULLY CONFORM TO JEDEC MO-229 REGISTRATION
- DIMENSIONS ARE IN MILLIMETERS.
- DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.
- LAND PATTERN RECOMMENDATION IS EXISTING INDUSTRY LAND PATTERN.
- DRAWING FILENAME: MKT-MLP06Lrev4.





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